Publication List

Refereed Journal Paper

1. Chii-Chang Chen, **Tao-Hung Hsueh**, Yi-Sheng Ting, Gou-Chung Chi, Chin-An Chang, and S. C. Wang, "Thermal annealing effects on the optical gain of InGaN/GaN quantum well structures," **Solid-State Electronics**. 47, 575 (2003).
2. H. C. Kuo, Y. S. Chang, F. Y. Lai, **T. H. Hsueh**, L. H. Lai, and S. C. Wang, "High speed modulation of 850 nm InGaAsP/InGaP strain-compensated VCSELs," **Electronics Letters** 39, 1051 (2003).
3. Fang-I Lai, **Tao-Hung Hsueh**, Ya-hsien Chang, Wen-chun Shu, Li-Hung Lai, H. C. Kuo and S. C. Wang, "Performance of 850 nm VCSEL utilizing Si implant induced disordering," **Solid State Electronics** 47, 1805 (2003).
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5. H. W. Huang, C. C. Kao, **T. H. Hsueh**, C. C. Yu, C. F. Ling, J. T. Chu, H. C. Kuo, S. C. Wang, "Fabrication of GaN-based nanorod light emitting diodes using self-assemble nickel nano-mask and inductively coupled plasma," **Materials Science & Engineering B** 113, 125 (2004).
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10. **Tao-Hung Hsueh**, Hung-Wen Huang, Chih-Chiang Kao, Ya-Hsien Chang, Miao-Chia Ou-Yang, Hao-Chung Kuo and Shing-Chung Wang, "InGaN/GaN Multi-Quantum-Well Nanorods Fabricated by Plasma Etching Using Self-assembled Nickel Nano-masks" IUMRS, Taiwan ID 168, (2004).
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13. **T. H. Hsueh**, J. K. Sheu, J. Y. Chu, H. W. Huang, C. C. Kao, H. C. Kuo and S. C. Wang, "Characteristics of Light Output Efficiency in InGaN-based Micro-Light-Emitting Diodes", APWS (2005).